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## ABSTRACT OF THE DISCLOSURE

An  $\mathrm{SiN}_{x}$  film is formed on partial side surfaces and an electrode forming surface excluding an n-side electrode of a first contact layer, the side surfaces of each layer, the upper surface of a second cladding layer and the side surfaces of a ridge portion. An  $\mathrm{SiO}_{y}$  film is formed on the  $\mathrm{SiN}_{x}$  film. The  $\mathrm{SiN}_{x}$  film and the  $\mathrm{SiO}_{y}$  film form a dielectric film.